
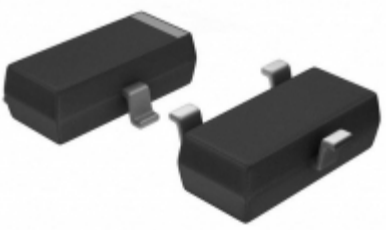
	<p>SI2316DS-T1-E3</p>
	<p>Hersteller-Teilenummer: SI2316DS-T1-E3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N-CH 30V 2.9A SOT23-3</p> <p>Datenblätter:  SI2316DS-T1-E3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 92406 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2316DS-T1-E3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 30V 2.9A SOT23-3
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	92406 pcs Stock
Hersteller Standard Vorlaufzeit	33 Weeks
detaillierte Beschreibung	N-Channel 30V 2.9A (Ta) 700mW (Ta) Surface Mount
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	700mW (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	2.9A (Ta)
Rds On (Max) @ Id, Vgs	50 mOhm @ 3.4A, 10V
VGS (th) (Max) @ Id	800mV @ 250µA (Min)
Gate Charge (Qg) (Max) @ Vgs	7nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	215pF @ 15V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI2316DS-T1-E3TR

SI2316DS-T1-E3 ist neu im Original, Suche SI2316DS-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2316DS-T1-E3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI2316DS-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2317DS-T1-E3 VISHAY/PL SI2317DS-T1-E3 VISHAY/PL</p>	 <p>SI2316BDS-T1-E3 Vishay / Siliconix MOSFET N-CH 30V 4.5A SOT-23</p>	 <p>SI2316DS-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 2.9A SOT23-3</p>	 <p>SI2316DS 89K SI2316DS 89K</p>
 <p>SI2316BDS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 4.5A SOT23-3</p>	 <p>SI2318ADS-T1-GE3 V SI2318ADS-T1-GE3 V</p>	 <p>SI2317DS VISHAY SI2317DS VISHAY</p>	 <p>SI2316DS-T1-E3 Vishay / Siliconix MOSFET N-CH 30V 2.9A SOT23-3</p>

heiße Teile

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|--------------------|--------------------|--------------------|--------------------|--------------------|
| ⊛ SI2313DS-T1-E3 | ↔ SI2313DS-T1-GE3 | ⇒ SI2314DS | D SI2314DS-T1-E3 | ↔ SI2314DS-T1-GE3 |
| ⊣ SI2314EDS | ⊛ SI2314EDS-T1-E3 | D SI2314EDS-T1-E3 | ⇒ SI2314EDS-T1-GE3 | ↔ SI2314EDS-T1-GE3 |
| ⊛ SI2315BDS | ⊣ SI2315BDS-T1-E3 | ⊛ SI2315BDS-T1-E3 | ↔ SI2315BDS-T1-GE3 | ↔ SI2315BDS-T1-GE3 |
| D SI2315DS | ⊛ SI2315DS-T1 | ⊣ SI2315DS-T1-E3 | ⊛ SI2315DS-T1-GE3 | ↔ SI2316-DS |
| ⇒ SI2316BDS-T1-E3 | ↔ SI2316BDS-T1-E3 | ⊛ SI2316BDS-T1-GE3 | ⊣ SI2316BDS-T1-GE3 | ↔ SI2316DS |
| ↔ SI2316DS-T1-E3 | ⇒ SI2316DS-T1-GE3 | D SI2316DS-T1-GE3 | ⊛ SI2317DS | ⊣ SI2317DS-T1-E3 |
| ⊛ SI2318ADS-T1-GE3 | D SI2318BDS-T1-E3 | ⇒ SI2318BDS-T1-GE3 | ↔ SI2318CDS-T1-E3 | ↔ SI2318CDS-T1-GE3 |
| ⊣ SI2318CDS-T1-GE3 | ⊛ SI2318DS | ↔ SI2318DS-T1-E3 | ⇒ SI2318DS-T1-E3 | ↔ SI2318DS-T1-GE3 |
| ⊛ SI2318DS-T1-GE3 | ⊣ SI2319ADS-T1-GE3 | ⊛ SI2319C95TF | D SI2319CDS-T1-E3 | ↔ SI2319CDS-T1-GE3 |
| ↔ SI2319CDS-T1-GE3 | ⊛ SI2319DDS-T1-GE3 | ⊣ SI2319DS | ⊛ SI2319DS-T1-E3 | ↔ SI2319DS-T1-E3 |

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